

DUAL DOPED POLYSILICON AND SILICON GERMANIUM ETCH

ABSTRACT OF THE DISCLOSURE

5 A method for etching a stack with at least one silicon germanium layer over a
substrate in a processing chamber is provided. A silicon germanium etch is provided.
An etchant gas is provided into the processing chamber, wherein the etchant gas
comprises HBr, an inert diluent, and at least one of O₂ and N₂. The substrate is cooled
to a temperature below 40° C. The etching gas is transformed to a plasma to etch the
10 silicon germanium layer.